TOSHIBA GTR Module Silicon N Channel IGBT

# MG50Q1ZS50

## High Power Switching Applications Motor Control Applications

• High input impedance

• High speed :  $t_f = 0.3 \mu s \text{ (max)}$ 

@Inductive load

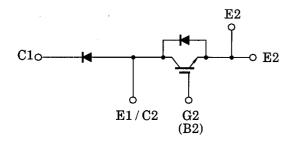
• Low saturation voltage

:  $V_{CE (sat)} = 3.6 \text{ V (max)}$ 

• Enhancement-mode

• The electrodes are isolated from case.

#### **Equivalent Circuit**



## **Maximum Ratings (Ta = 25°C)**

	Unit: mm
3-M5 E2 3-M5 E2 1 1 1 1 1 1 1 1 1 1 1 1 1	- FAST-ON-TAB#110 2-\$5.51 4 ± 0.6 35 ± 0.6 35 ± 0.6 35 ± 0.6
4±0.5 4±0.5 9.9±0 18±0.5 19±0.5 18±0.5	27±0.5 27±0.5 27±0.5 27±0.5 27±0.5
91±0.5	33.3±0.5
JEDEC —	
JEITA —	
TOSHIBA 2-94D	)7A

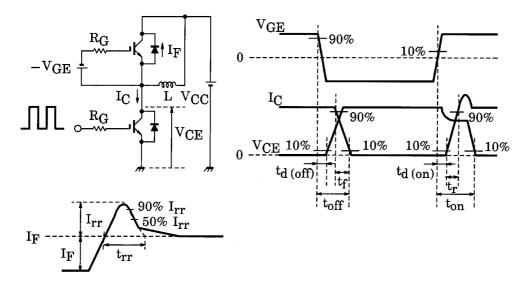
Weight: 202g

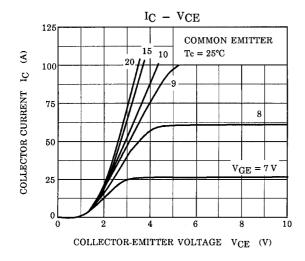
Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		$V_{CES}$	1200	V	
Gate-emitter voltage		V <sub>GES</sub>	±20	V	
Reverse voltage		V <sub>R</sub>	1200	٧	
Collector current	DC	I <sub>C</sub> (25°C / 80°C)	78 / 50	А	
	1ms	I <sub>CP</sub> (25°C / 80°C)	156 / 100		
Forward current	DC	I <sub>F</sub>	50	A	
	1ms	I <sub>FM</sub>	100		
Collector power dissipation (Tc = 25°C)		PC	400	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	<b>−</b> 40 ~ 125	°C	
Isolation voltage		V <sub>Isol</sub>	2500 (AC 1 minute)	V	
Screw torque (Terminal / mounting)		_	3/3	N·m	

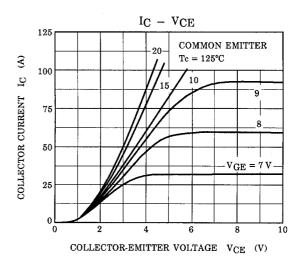
#### **Electrical Characteristics (Ta = 25°C)**

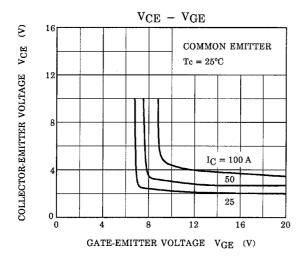
Cha	Characteristics Symbol Test Condition		on	Min	Тур.	Max	Unit	
Gate leakage current		I <sub>GES</sub>	V <sub>GE</sub> = ±20V, V <sub>CE</sub> = 0		_	_	±500	nA
Collector cut-off current		I <sub>CES</sub>	V <sub>CE</sub> = 1200V, V <sub>GE</sub> = 0		-	_	1.0	mA
Gate-emitter cut-off voltage		V <sub>GE (off)</sub>	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 5V		3.0	_	6.0	V
Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	I <sub>C</sub> = 50A, V <sub>GE</sub> = 15V	T <sub>j</sub> = 25°C	-	2.8	3.6	V
				T <sub>j</sub> = 125°C	-	3.1	4.0	
Input capacitance	,	C <sub>ies</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0, f = 1MHz		_	6.0	_	nF
Switching time	Turn-on delay time	t <sub>d (on)</sub>			-	0.05	_	
	Rise time	t <sub>r</sub>	Inductive load $V_{CC}$ = 600 $V_{IC}$ = 50 A $V_{GE}$ = ±15 $V_{RG}$ = 24 $\Omega$		-	0.05	_	
	Turn-on time	t <sub>on</sub>			_	0.2	_	μs
	Turn-off delay time	t <sub>d (off)</sub>			_	0.5	_	
	Fall time	t <sub>f</sub>		(Note 1)	_	0.1	0.3	
	Turn-off time	t <sub>off</sub>			_	0.6	_	
Reverse current		I <sub>R</sub>	V <sub>R</sub> = 1200 V		_	_	1.0	mA
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 50 A, V <sub>GE</sub> = 0		-	2.4	3.5	V
Reverse recovery time		t <sub>rr</sub>	$I_F = 50 \text{ A}, V_{GE} = -10 \text{ V},$ di / dt = 700 A / $\mu$ s (Note 1)		_	0.1	0.25	μs
Thermal resistance		R <sub>th (j-c)</sub>	Transistor stage		_	_	0.31	°C / \\\
			Diode stage		_	_	0.94	°C/W

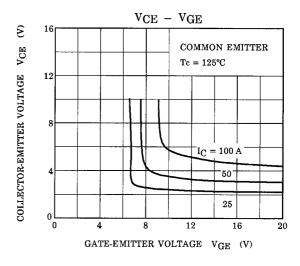
Note 1: Switching time and reverse recovery time test circuit & timing chart

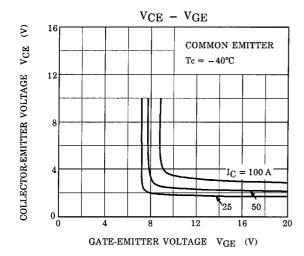


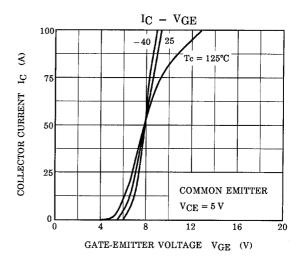




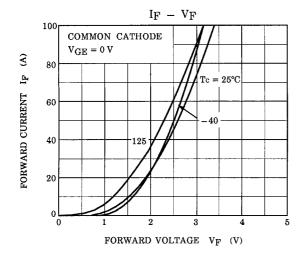


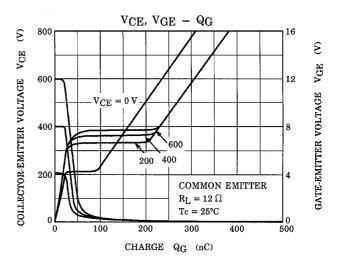


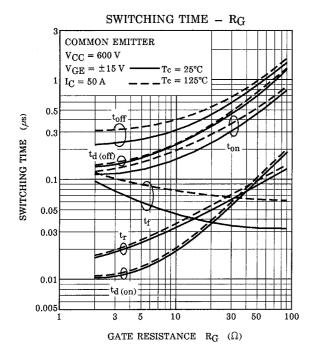


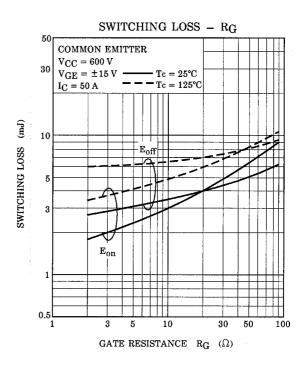


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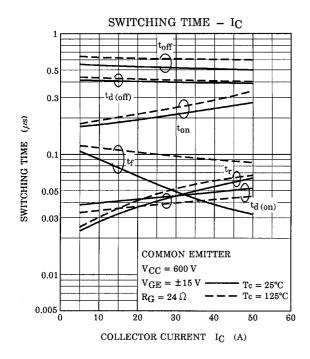


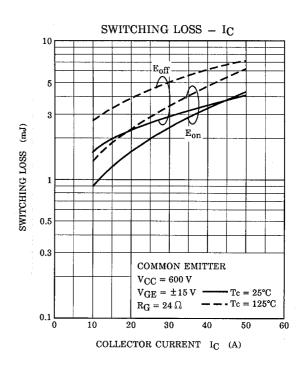


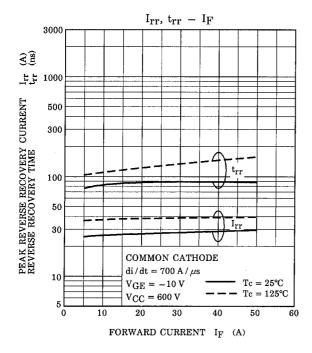


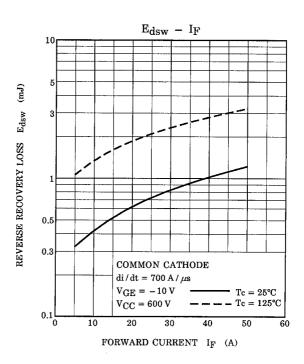


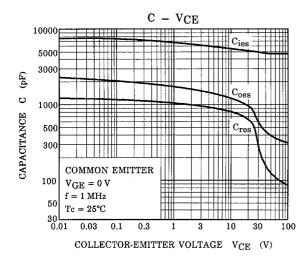
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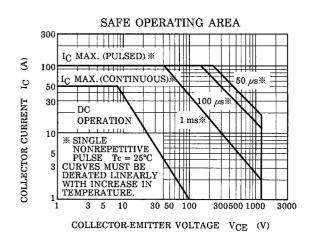


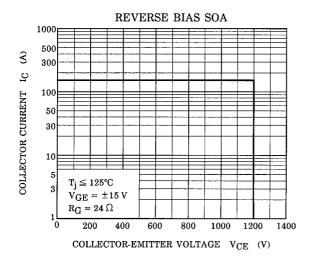


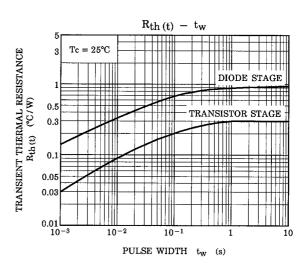


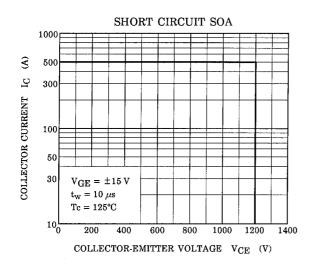












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